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PATENT
740756-1638

THE UNITED STATES PATENT AND TRADEMARK OFFICE

#49/K
7/11/02
Hayes

In re PATENT application of:

Hisashi OHTANI et al.

Application No.: 08/807,737

Filed: February 27, 1997

For: METHOD FOR MANUFACTURING
SEMICONDUCTOR DEVICE

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)
) Art Unit: 2813

)
) Examiner: Evan T. PERT

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

March 19, 2002

Dear Sir:

In response to the Examiner's non-Final Office Action mailed December 19, 2001 please
consider the following amendment and remarks in connection with the above identified
application.

IN THE CLAIMS:

Please amend claim 84 as follows:

84. (Twice Amended) A method of manufacturing a semiconductor device comprising
the steps of:

KL forming a silicon nitride film containing at least one of hydrogen and oxygen over
a substrate;

depositing a semiconductor film comprising amorphous silicon on said silicon
nitride film;

disposing a metal in contact with at least a selected portion of said semiconductor
film;

heating said semiconductor film and said metal to crystallize said semiconductor
film; and

forming a channel region,

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